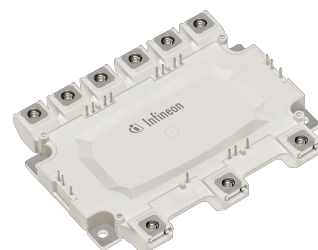


HybridPACK™ DC6 module with Trench/Fieldstop IGBT3 and emitter controlled 3 diode and NTC

Features

- Electrical features
 - $V_{CES} = 700 \text{ V}$
 - $I_{C \text{ nom}} = 400 \text{ A} / I_{CRM} = 800 \text{ A}$
 - Increased blocking voltage capability to 705 V
 - $V_{CE,sat}$ with positive temperature coefficient
 - Low $V_{CE,sat}$
 - Low switching losses
 - Low inductive design
 - $T_{vj,op} = 150^{\circ}\text{C}$
 - Short-time extended operation temperature $T_{vj,op} = 175^{\circ}\text{C}$
- Mechanical features
 - 2.5 kV AC 1 minute insulation
 - Al_2O_3 substrate with low thermal resistance
 - Integrated NTC temperature sensor
 - High mechanical robustness
 - RoHS compliant



Potential applications

- (Hybrid) electrical vehicles (H)EV
- Motor drives
- Optimized for automotive applications with DC link voltages up to 450 V

Description

Infineon's HybridPACK™ 1 DC6 is a variant of the HybridPACK™ 1 power module family with increased continuous current capability and a reduced stray inductance.

Like all HybridPACK™ 1 products the HybridPACK™ 1 DC6 is an automotive qualified powermodule designed for electric vehicle applications. Designed for a 150°C junction operation temperature, with a 30 hour limited 175°C capacity the module accommodates a 3-phase Six-Pack configuration of Trench-Field-Stop IGBT3 and matching emitter controlled diodes. The HybridPACK™ 1 power module family is built on Infineon's long time experience in the development of IGBT power modules, intense research efforts of new material combinations and assembly technologies. HybridPACK™ 1 DC6 is suitable for air or liquid cooling. The copper base plate combined with high-performance ceramic substrate and Infineon's enhanced wire-bonding process provides unparalleled thermal and power cycling capability and highest reliability for mild hybrid inverter or generator applications. For a compact design the driver stage PCB can easily be soldered on top of the module. All power connections are realized with screw terminals.

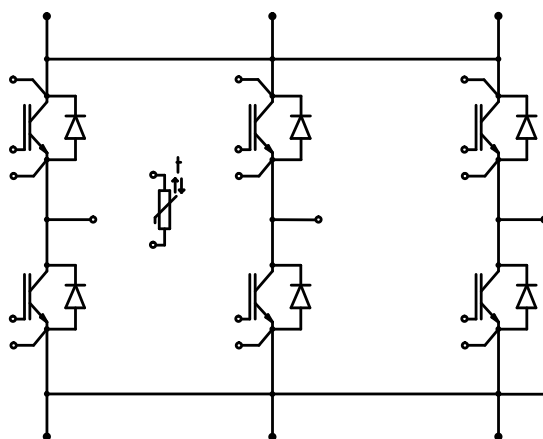


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{creep}	terminal to heatsink	12.0	mm
Creepage distance	d_{creep}	terminal to terminal	6.1	mm
Clearance	d_{clear}	terminal to heatsink	12.0	mm
Clearance	d_{clear}	terminal to terminal	6.1	mm
Comparative tracking index	CTI		>200	

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Maximum RMS module terminal current ¹⁾	$I_{t,rms}$	$T_{terminal} = 150 \text{ °C}$, $T_c = 25 \text{ °C}$	320	A

1) DC-collector current limited by internal busbar.

Table 3 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	$L_{s,CE}$			16.0		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T = 25 \text{ °C}$, per switch		1.00		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for module mounting	M	Screw M5 baseplate to heatsink	3.0		6.0	Nm
Terminal connection torque	M	Screw M6	3.0		6.0	Nm
Weight	G			510		g

Note: Mounting according to valid application note AN 2010-08 Mounting Instruction HybridPACK™ 1.

2 IGBT, Inverter

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25 \text{ °C}$	705	V

(table continues...)

Table 4 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Continuous DC collector current	$I_{C,nom}$	$T_c = 65\text{ °C}, T_{vj,max} = 175\text{ °C}$	400	A
Continuous DC collector current	I_C	$T_c = 25\text{ °C}, T_{vj,max} = 175\text{ °C}$	500	A
Repetitive peak collector current	I_{CRM}	$t_P = 1\text{ ms}$	800	A
Total power dissipation	P_{tot}	$T_c = 25\text{ °C}, T_{vj,max} = 175\text{ °C}$	1250	W
Gate-emitter peak voltage	V_{GES}		±20	V

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE,sat}$	$I_C = 400\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$		1.45	1.70	V
			$T_{vj} = 125\text{ }^{\circ}\text{C}$		1.60		
			$T_{vj} = 150\text{ }^{\circ}\text{C}$		1.70		
Gate threshold voltage	$V_{GE,th}$	$I_C = 6.4\text{ mA}, V_{CE} = V_{GE}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$	4.9	5.8	6.5	V
Gate charge	Q_G	$V_{GE} = \pm 15\text{ V}$			4.3		μC
Internal gate resistor	$R_{G,int}$		$T_{vj} = 25\text{ }^{\circ}\text{C}$		1.0		Ω
Input capacitance	C_{ies}	$f = 1\text{ MHz}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$		26.0		nF
Reverse transfer capacitance	C_{res}	$f = 1\text{ MHz}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$		0.76		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 450\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$			0.1	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$			400	nA
Turn-on delay time, inductive load	$t_{d,on}$	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}, V_{GE} = \pm 15\text{ V}, R_{G,on} = 1.8\text{ }\Omega$	$T_{vj} = 25\text{ }^{\circ}\text{C}$		0.12		μs
			$T_{vj} = 125\text{ }^{\circ}\text{C}$		0.12		
			$T_{vj} = 150\text{ }^{\circ}\text{C}$		0.12		
Rise time, inductive load	t_r	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}, V_{GE} = \pm 15\text{ V}, R_{G,on} = 1.8\text{ }\Omega$	$T_{vj} = 25\text{ }^{\circ}\text{C}$		0.08		μs
			$T_{vj} = 125\text{ }^{\circ}\text{C}$		0.08		
			$T_{vj} = 150\text{ }^{\circ}\text{C}$		0.08		
Turn-off delay time, inductive load	$t_{d,off}$	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}, V_{GE} = \pm 15\text{ V}, R_{G,off} = 1.8\text{ }\Omega$	$T_{vj} = 25\text{ }^{\circ}\text{C}$		0.36		μs
			$T_{vj} = 125\text{ }^{\circ}\text{C}$		0.40		
			$T_{vj} = 150\text{ }^{\circ}\text{C}$		0.40		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Fall time, inductive load	t_f	$I_C = 400\text{ A}$, $V_{CE} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{G,off} = 1.8\ \Omega$	$T_{vj} = 25\text{ °C}$	0.02		μs
			$T_{vj} = 125\text{ °C}$	0.03		
			$T_{vj} = 150\text{ °C}$	0.03		
Turn-on energy loss per pulse	E_{on}	$I_C = 400\text{ A}$, $V_{CE} = 300\text{ V}$, $L_\sigma = 16\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{G,on} = 1.8\ \Omega$	$T_{vj} = 25\text{ °C}$	5.1		mJ
			$T_{vj} = 125\text{ °C}$	6.8		
			$T_{vj} = 150\text{ °C}$, $di/dt = 4500\text{ A}/\mu\text{s}$	7.3		
Turn-off energy loss per pulse	E_{off}	$I_C = 400\text{ A}$, $V_{CE} = 300\text{ V}$, $L_\sigma = 16\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{G,off} = 1.8\ \Omega$	$T_{vj} = 25\text{ °C}$	9.1		mJ
			$T_{vj} = 125\text{ °C}$	12.0		
			$T_{vj} = 150\text{ °C}$, $du/dt = 3400\text{ V}/\mu\text{s}$	12.5		
SC data	I_{SC}	$V_{CC} = 360\text{ V}$, $V_{CEmax} =$ $V_{CES} - L_{sCE} \cdot di/dt$	$T_{vj} = 25\text{ °C}$, $t_p \leq 8\ \mu\text{s}$	2800		A
			$T_{vj} = 150\text{ °C}$, $t_p \leq 6\ \mu\text{s}$	2000		
Thermal resistance, junction to case	$R_{th,j-c}$	per IGBT			0.120	K/W
Thermal resistance, case to heat sink	$R_{th,c-h}$	per IGBT $\lambda_{paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		0.080		K/W
Temperature under switching conditions	$T_{vj,op}$	t_{op} continuous	-40		150	$^{\circ}\text{C}$
		$t_{op,max}$ 30h over life time, for 10s within period of 10min	150		175	

Note: DC-collector current limited by power terminals.

3 Diode, Inverter

Table 6 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\text{ °C}$	705	V
Continuous DC forward current	$I_{F,nom}$		400	A
Repetitive peak forward current	I_{FRM}	$t_p = 1\text{ ms}$	800	A

(table continues...)

Table 6 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
I^2t - value	I^2t	$V_R = 0 \text{ V}$, $t_p = 10 \text{ ms}$	$T_{vj} = 125 \text{ °C}$	A^2s
			$T_{vj} = 150 \text{ °C}$	
			8800	
			8500	

Table 7 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 400 \text{ A}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$		1.55	V
			$T_{vj} = 125 \text{ °C}$		1.50	
			$T_{vj} = 150 \text{ °C}$		1.45	
Peak reverse recovery current	I_{rm}	$I_F = 400 \text{ A}$, $V_{GE} = -15 \text{ V}$, $V_R = 300 \text{ V}$	$T_{vj} = 25 \text{ °C}$		205	A
			$T_{vj} = 125 \text{ °C}$		295	
			$T_{vj} = 150 \text{ °C}$, $-di_F/dt = 4500 \text{ A}/\mu\text{s}$		305	
Recovered charge	Q_r	$I_F = 400 \text{ A}$, $V_{GE} = -15 \text{ V}$, $V_R = 300 \text{ V}$	$T_{vj} = 25 \text{ °C}$		15.0	μC
			$T_{vj} = 125 \text{ °C}$		32.0	
			$T_{vj} = 150 \text{ °C}$, $-di_F/dt = 4500 \text{ A}/\mu\text{s}$		34.0	
Reverse recovery energy	E_{rec}	$I_F = 400 \text{ A}$, $V_{GE} = -15 \text{ V}$, $V_R = 300 \text{ V}$	$T_{vj} = 25 \text{ °C}$		3.35	mJ
			$T_{vj} = 125 \text{ °C}$		6.90	
			$T_{vj} = 150 \text{ °C}$, $-di_F/dt = 4500 \text{ A}/\mu\text{s}$		8.10	
Thermal resistance, junction to case	$R_{th,j-c}$	per diode			0.200	K/W
Thermal resistance, case to heat sink	$R_{th,c-h}$	per diode $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$		0.085		K/W
Temperature under switching conditions	$T_{vj,op}$	t_{op} continuous	-40		150	$^{\circ}\text{C}$
		$t_{op,max}$ 30h over life time, for 10s within period of 10min	150		175	

Note: Diode forward current limited by power terminals.

4 NTC-Thermistor

Table 8 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25 \text{ °C}$		5		k Ω

(table continues...)

Table 8 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100\text{ °C}$, $R_{100} = 493\ \Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25\text{ °C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$		3433		K

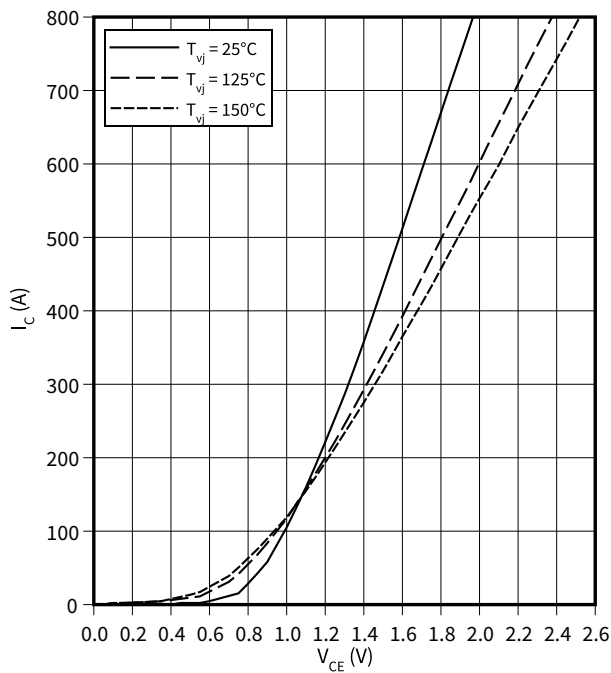
Note: Specification according to the valid application note.

5 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

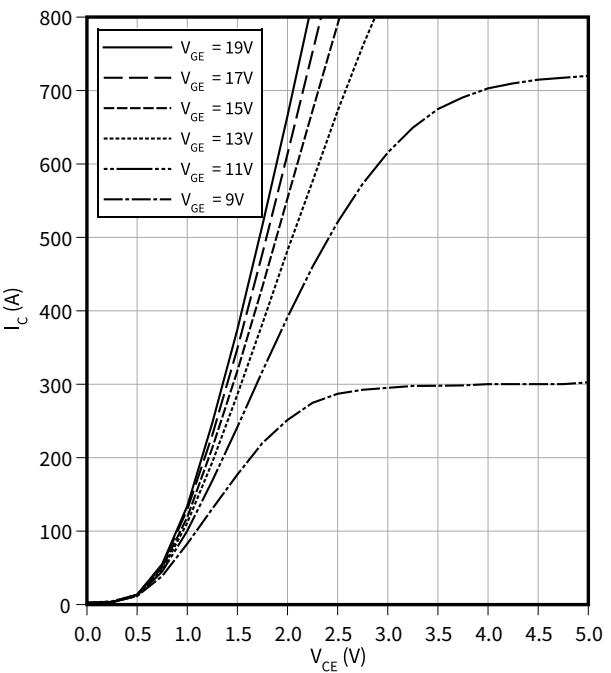
$V_{GE} = 15\text{ V}$



Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

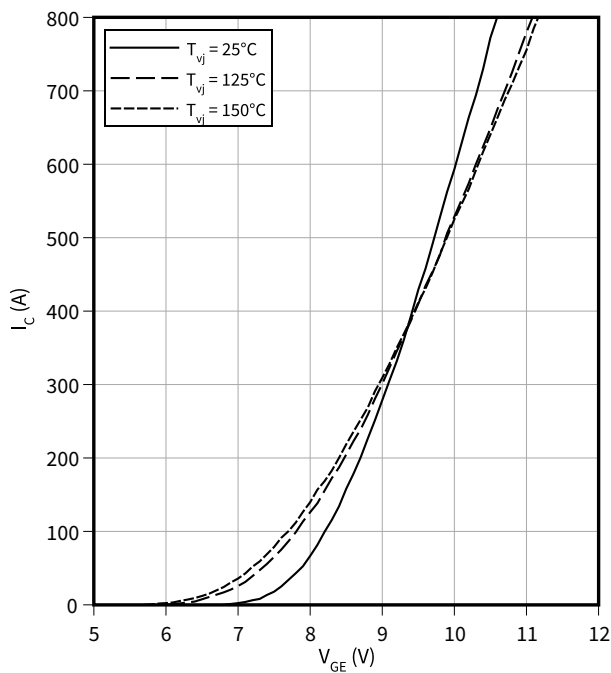
$T_{vj} = 150\text{ °C}$



Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

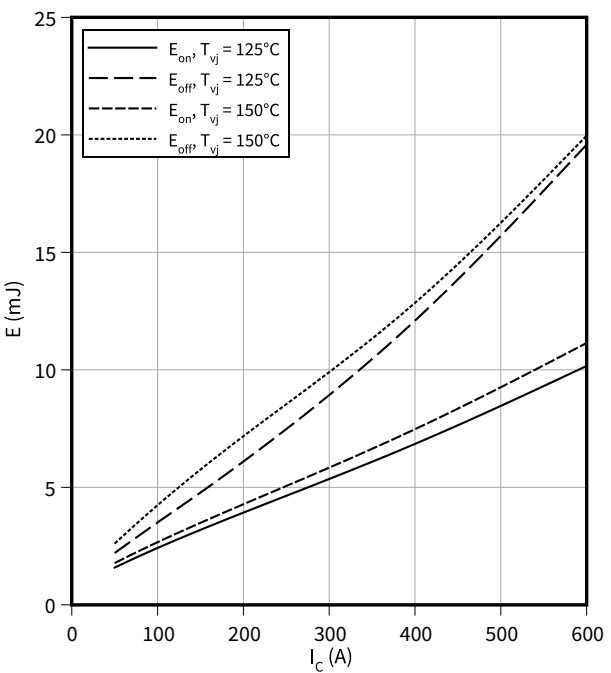
$V_{CE} = 20\text{ V}$



Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

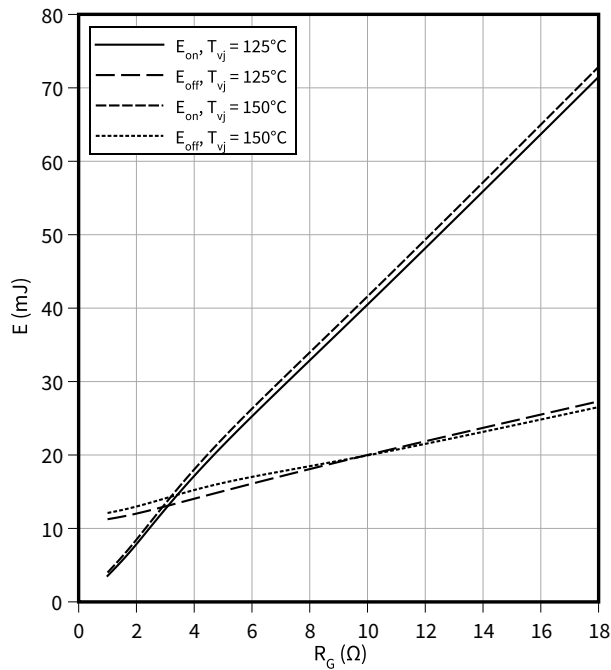
$R_{G,off} = 1.8\text{ }\Omega$, $R_{G,on} = 1.8\text{ }\Omega$, $V_{CE} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$



5 Characteristics diagrams

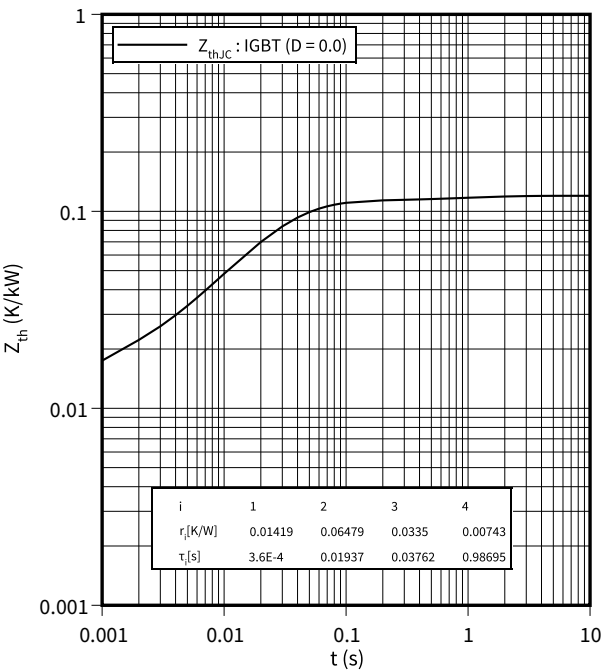
Switching losses (typical), IGBT, Inverter

$E = f(R_G)$
 $V_{CE} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $I_C = 400\text{ A}$



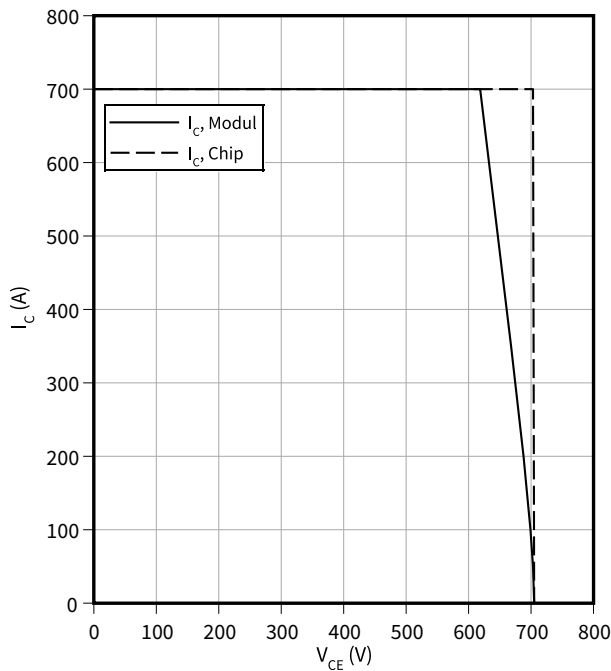
Transient thermal impedance, IGBT, Inverter

$Z_{th} = f(t)$



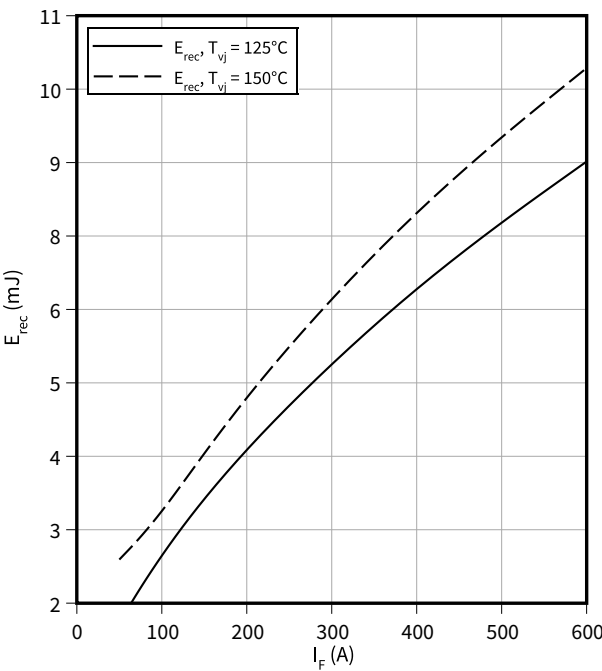
Reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$
 $T_{vj} = 150\text{ °C}$, $R_{G,off} = 1.8\text{ Ω}$, $V_{GE} = \pm 15\text{ V}$



Switching losses (typical), Diode, Inverter

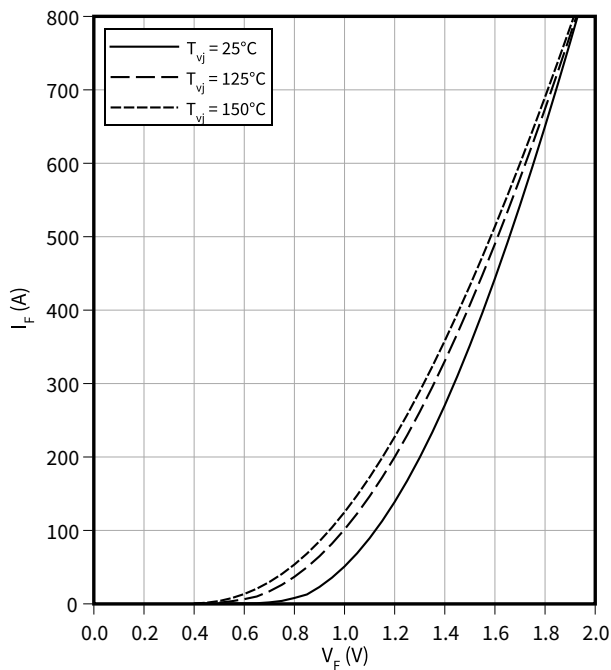
$E_{rec} = f(I_F)$
 $R_{Gon} = 1.8\text{ Ω}$, $V_{CE} = 300\text{ V}$



5 Characteristics diagrams

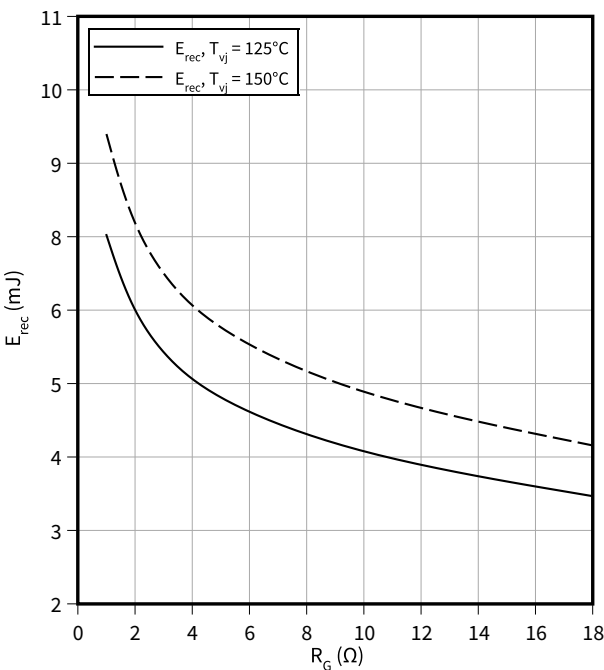
Forward characteristic (typical), Diode, Inverter

$I_F = f(V_F)$



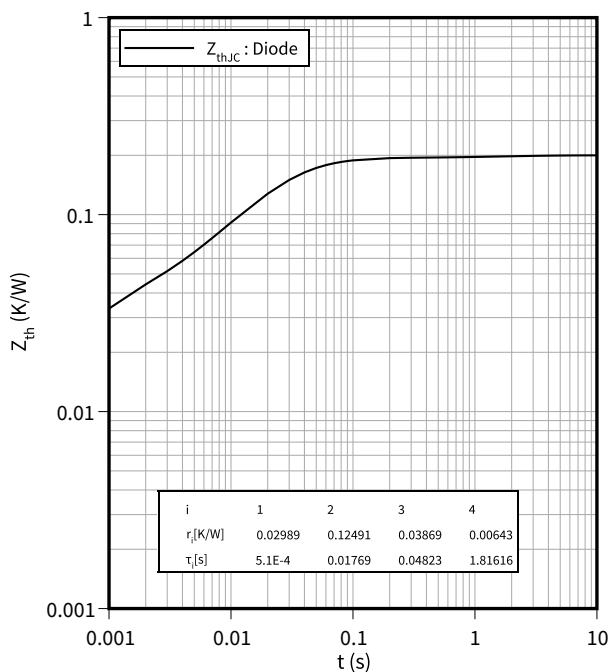
Switching losses (typical), Diode, Inverter

$E_{rec} = f(R_G)$
 $V_{CE} = 300\text{ V}, I_F = 400\text{ A}$



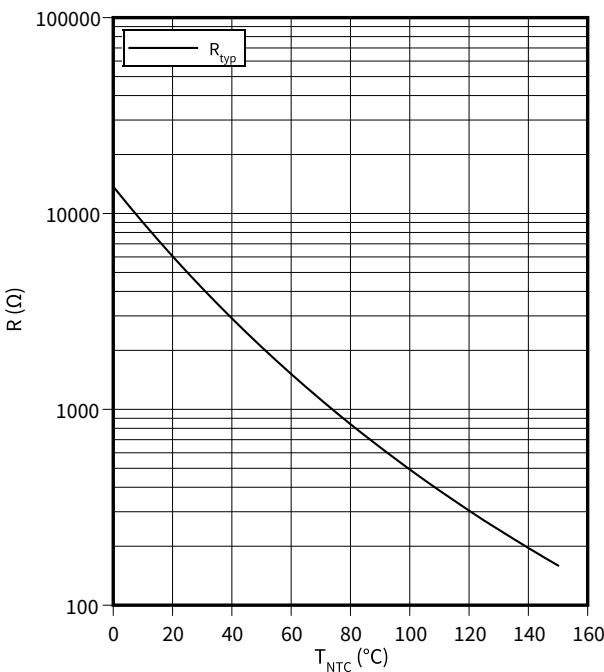
Transient thermal impedance , Diode, Inverter

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



6 Circuit diagram

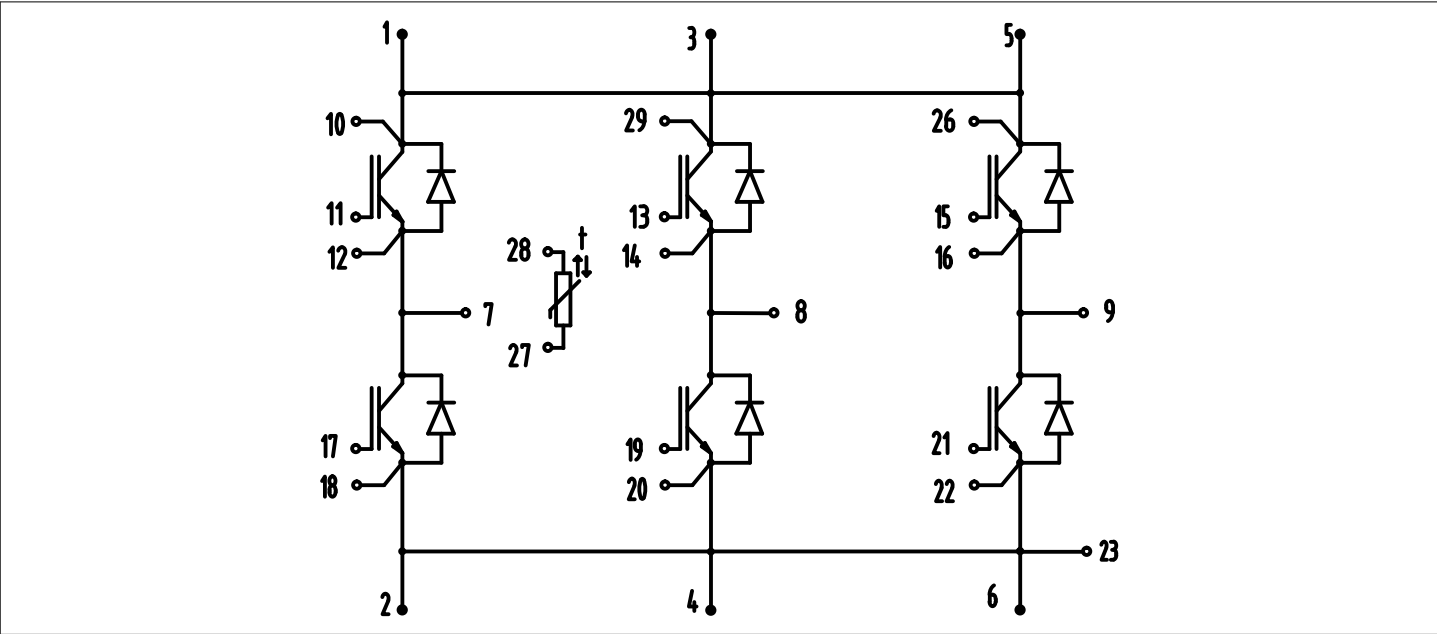


Figure 1

7 Package outlines

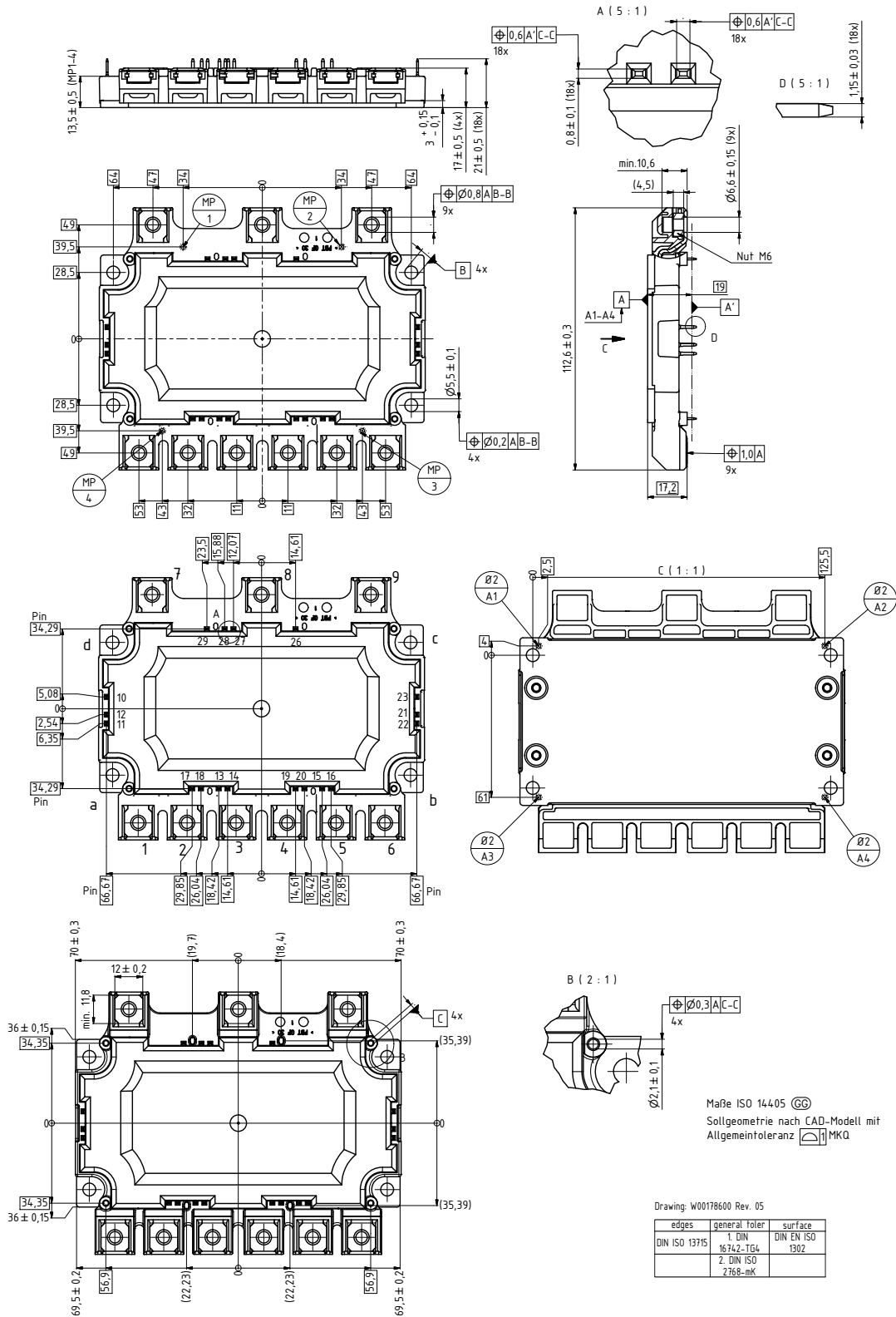


Figure 2

8 Module label code

Module label code				
Code format	Data Matrix		Barcode Code128	
Encoding	ASCII text		Code Set A	
Symbol size	16x16		23 digits	
Standard	IEC24720 and IEC16022		IEC8859-1	
Code content	<i>Content</i> Module serial number Module material number Production order number Date code (production year) Date code (production week)	<i>Digit</i> 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23		<i>Example</i> 71549 142846 55054991 15 30
Example	  71549142846550549911530 71549142846550549911530			

Packing label code				
Code format	Barcode Code128			
Encoding	Code Set A			
Symbol size	34 digits			
Standard	IEC8859-1			
Code content	<i>Content</i> Module serial number Module material number Production order number Date code (production year) Date code (production week)	<i>Identifier</i> X 1T S 9D Q	<i>Digit</i> 2 – 9 12 – 19 21 – 25 28 – 31 33 – 34	<i>Example</i> 95056609 2X0003E0 754389 1139 15
Example	 X950566091T2X0003E0S754389D1139Q15			

Figure 3

Revision history

Document revision	Date of release	Description of changes
V1.0	2015-04-24	
V2.0	2015-11-09	
V3.0	2017-03-07	
n/a	2020-10-05	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.10	2021-12-21	Adjustment of package outline

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